# High-voltage Switching Transistor (Camera strobes and Telephone, Power supply) (-400V, -0.1A)2SA1759

#### Features

- 1) High breakdown voltage. (BVCEO=-400V)
- 2) Low saturation voltage, typically VCE(sat) = -0.2V at Ic / IB = -20mA / -2mA.
- 3 ) High switching speed, typically tf=1  $\mu$ s at lc=100mA.
- 4) Wide SOA (safe operating area).
- 5) Complements the 2SA4505.

#### Packaging specifications and hre

Туре	2SA1759		
Package	MPT3		
hfe	Р		
Marking	AH*		
Code	T100		
Basic ordering unit (pieces)	3000		

\* Denotes hre

Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	ВVсво	-400	-	—	V	Ic=-50 μ A
Collector-emitter breakdown voltage	BVCEO	-400	-	_	V	Ic=-1mA
Emitter-base breakdown voltage	<b>BV</b> EBO	-7	-	—	V	$I_E = -50 \mu A$
Collector cutoff current	Ісво	-	-	-10	μA	VcB=-400V
Emitter cutoff current	lebo	-	-	-10	μA	VEB=-6V
Collector-emitter saturation voltage	VCE(sat)	-	-0.2	-0.5	V	Ic/IB=-20mA/-2mA
Base-emitter saturation voltage	VBE(sat)	-	-	-1.2	V	Ic/IB=-20mA/-2mA
DC current transfer ratio	hre	82	-	180	—	Vce=-10V, lc=-10mA
Transition frequency	f⊤	-	12	_	MHz	Vce=-10V, le=10mA, f=5MHz
Output capacitance	Cob	-	13	—	pF	Vcb=-10V, le=0A, f=1MHz
Turn-on time	ton	-	0.7		μs	Ic=-100mA RL=1.5kΩ
Storage time	tsıg	-	1.8	—	μs	IB1=-IB2=-10mA
Fall time	tr	-	1	_	μs	Vcc~-150V

# Power Transistor (400V, 0.1A)

## 2SC4505 / 2SC4620

#### Features

- 1) High breakdown voltage. (BVCEO=400V)
- 2 ) Low saturation voltage, typically VcE(sat) =0.05V at Ic / Is=10mA / 1mA.
- 3) High switching speed, typically tf=1.7  $\mu$ s at Ic=100mA
- 4) Complements the 2SC4505 and the 2SA1759.

#### Packaging specifications and hre

Туре	2SC4505	2SC4620
Package	MPT3	ATV
hfe	PQ	Q
Marking	CE*	—
Code	T100	TV2
Basic ordering unit (pieces)	1000	2500

\* Denotes hre

#### Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base breakdown voltage	ВУсво	400	—	—	V	Ic=50 μ A	
Collector-emitter breakdown voltage	BVCEO	400	-	-	V	Ic=1mA	
Emitter-base breakdown voltage	<b>BV</b> EBO	7	-	—	V	Iε=50 μ A	
Collector cutoff current	Ісво	_	-	10	μA	Vcb=400V	
Emitter cutoff current	IEBO	—	-	10	μA	VEB=6V	
Collector-emitter saturation voltage	VCE(sat)	—	0.05	0.5	V	Ic=10mA, Is=1mA	
Base-emitter saturation voltage	VBE(sat)	—	-	1.5	V	Ic=10mA, Is=1mA	
DC current transfer ratio	hfe	82	-	270	-	Vce/lc=10V/10mA	
Transition frequency	f⊤	_	20	—	MHz	Vce=10V, Ie=-10mA, f=10MHz	
Output capacitance	Cob	-	7	-	pF	Vcb=10V, IE=0A, f=1MHz	
Turn-on time	ton	—	1	—	μs	Ic=100mA	
Storage time	taig	—	5.5	—	μs	IB1=-IB2=10mA	
Fall time	tf	—	1.7	—	μs	Vcc <u>~</u> −150V	

#### Absolute maximum ratings (Ta=25°C)

*	-			
Parameter	Symbol	Limits	Unit	
Collector-base voltage	Vсво	-400	V	
Collector-emitter voltage	VCEO	-400	V	
Emitter-base voltage	VEBO	-7	V	
Collector current	lc	-0.1	A(DC)	
		-0.2	A (Pulse) *1	
Collector power dissipation	Po	0.5	W	
		2 *2	vv	
Junction temperature	Tj	150	Ĵ	
Storage temperature	Tstg	-55~+150	Ç	

\*1 Single pulse, Pw=100ms

\*2 When mounted on a 40×40×0.7 mm ceramic board

● Absolute maximum ratings (Ta=25℃)

2SC4505

2SC4620

Symbol

Vсво

VCEO

Vebo

lc

ICP

Pc

Tj

Tsta

Limits

400

400

7

0.1

0.2

0.5

1

150

 $-55 \sim \pm 150$ 

Parameter

\* Single pulse Pw=20ms Duty=1/2

Collector-base voltage

Emitter-base voltage

Junction temperature

Storage temperature

Collector current

Collector power

dissipation

Collector-emitter voltage

Unit

ν

v

V

А

A

w

#### (96-97-A324)

(96-178-C300)



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